

Erik Friess

List of Publications by Year in descending order

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13
papers

600
citations

933447

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h-index

1125743

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g-index

13
all docs

13
docs citations

13
times ranked

209
citing authors

#	ARTICLE	IF	CITATIONS
1	Investigation of the relaxation of excess carriers in SiGe-heterostructures by photothermal measurement. Applied Surface Science, 1993, 63, 260-265.	6.1	1
2	Influence of growth conditions on the photoluminescence of pseudomorphic MBE grown Si _{1-x} Ge _x quantum wells. Journal of Crystal Growth, 1993, 127, 443-446.	1.5	9
3	Phosphorous doping in low temperature silicon molecular beam epitaxy. Applied Physics Letters, 1992, 60, 2237-2239.	3.3	30
4	Band gap luminescence in pseudomorphic Si _{1-x} Ge _x quantum wells grown by molecular beam epitaxy. Thin Solid Films, 1992, 222, 27-29.	1.8	32
5	Boron-doped Si/Ge superlattices and heterostructures. Thin Solid Films, 1992, 222, 150-153.	1.8	7
6	Photoluminescence studies of Si/Si _{1-x} Ge _x quantum wells and SiGe superlattices. Thin Solid Films, 1992, 222, 227-233.	1.8	30
7	Structural stability of short-period Si/Ge superlattices studied with Raman spectroscopy. Physical Review B, 1991, 44, 1772-1781.	3.2	68
8	Strain and confinement effects on optical phonons in short period (100) Si/Ge superlattices. Solid State Communications, 1990, 73, 203-207.	1.9	43
9	Confined optical modes in short period (110) Si/Ge superlattices. Solid State Communications, 1989, 69, 899-903.	1.9	38
10	Improvement of structural properties of Si/Ge superlattices. Thin Solid Films, 1989, 183, 95-103.	1.8	21
11	Silicon/germanium strained layer superlattices. Journal of Crystal Growth, 1989, 95, 431-438.	1.5	127
12	Symmetrically strained Si/Ge superlattices on Si substrates. Physical Review B, 1988, 38, 3599-3601.	3.2	142
13	Annealing effects in short period Si-Ge strained layer superlattices. Semiconductor Science and Technology, 1988, 3, 1166-1170.	2.0	52